

ENSC Batch No. _____ Wafers Started _____ Date _____
 Material _____ Orientation _____ Size _____ Thickness _____
 Resistivity _____ Type _____
 Wafer Vendor _____ Vendor Batch # _____ SFU P.O. _____

Process Step #	Process Conditions	Oper & Wafer #	Comments
			Wafers require a modified RCA clean immediately prior to diffusion .
_____A	Prepare furnace (tube 3) N2 @ 8 scfh. O2 @ 0. Ramp temp to 750/800C		
_____B	Pull boat and load wafers Pull <4"/min. 2 wafers/ source, in slots next to source, facing it. Dummies in empty slots .		
_____C	Push boat into furnace N2 @ 8 scfh. O2 @ 0 scfh. Temp = 800C. Push <4"/min.		
_____D	Stabilization at 800C N2 @ 8 scfh. O2 @ 0 scfh. Time = 10 min.		
_____E	Ramp to operating temp N2 @ 8 scfh. O2 @ 0 scfh.		
_____F	Diffusion N2 @ 8 scfh. O2 @ 0 scfh. Temp = oper. Set timer.		Time = _____min Temp = _____C Indicate desired resistivity, concentration or depth.
_____G	Ramp furnace down N2 @ 8 scfh. O2 @ 0. Set temp to 500C when diff'n over		
_____H	Pull boat, unload All zones < 800C. N2 @ 8 scfh. O2 @ 0. Pull <4"/min.		
_____I	Push boat N2 @ 8 scfh. Dummies next to sources. Push <4"/min.		
_____J	Return furnace to idle N2 @ 0.5-1.0 scfh. O2 @ 0.		
_____K	Inspect Visual, resistivity, etc.		